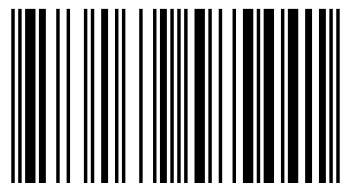


In the last couple of decades, the elastic strain engineering approach in nano-scaled silicon devices has been successfully implemented for different applications. Now a days, researchers are trying to incorporate such strain in different other materials such as Ge, GaAs, InGaAs, MoS2 etc. However, there are still some interesting areas remaining to extract further advantages of such strain technologies, which can be exploited for development of high performance CMOS devices and circuits, keeping the manufacturing cost and time under control.

Strain Engineering in Nano-scaled FETs



Dr. Kunal Sinha received his Ph.D. (Engg) degree in microelectronics from Indian Institute of Engineering Science and Technology – Shibpur (IEST-Shibpur) Howrah, India. His research area includes Strain Engineering in Nano-scale FET devices, Nano-scale FET devices as biosensor and optical sensor, Electrodynamic Screening in photo-voltaic panels etc



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Sinha, Chattopadhyay, Rahaman

Dr. Kunal Sinha
Dr. Sanatan Chattopadhyay
Prof. Hafizur Rahaman

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